XO-5-7-3.3V-LVCMOS-xMHz LVCMOS10 to 245MHz Clock Oscillator

Features and Benefits

Frequency Range 10 MHz to 245 MHz Output Frequency to six decimal places

Output Frequency Examples: 12.688375 MHz; 125.345678 MHz

7 mm x 5.0 mm x 1.80 mm ceramic SMD 6-pad ±50 ppm total stability over -40°C to 85°C

1 to 1.5 pico-second phase jitter (12KHz to 20 MHz)

LVCMOS output 3.3V supply

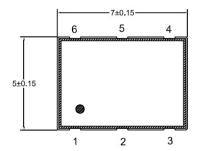
Typical Applications

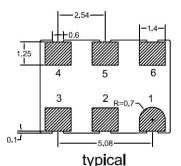
Gb Ethernet, SONET, Fibre channel, FPGA, and A/D clock reference devices

Description

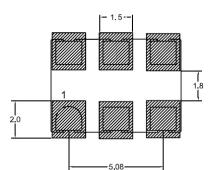
A new generation of low jitter / low power clock oscillators has been developed using the latest low noise integrated circuit topologies.

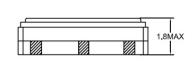
Mechanical Drawing & Pin Connections





Product XO **VCXO** Pad 1 High Enable Voltage Control Pad 2 No Connection High Enable Pad 3 Ground CMOS: Output LVPECL, LVDS: Pad 4 **Differential Output** CMOS: No connection LVPECL, Pad 5 LVDS: Complementary Output Pad 6 Supply voltage





bottom view

Dynamic Engineers Inc.

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Specifications

General Specifications	: at Ta=+	25°C,		
Output Logic Type		LVCMOS		
Frequency Range		10 ~ 245 MHz		
Load		15pF		
Power Supply Voltage (V _{DD})		$V_{DD} = +3.3 \text{V D.C.} \pm 5\%$		
Output "High" Voltage; V _{OH}		Voltage (V _{OD})	90% V _{DD}	
Output "Low" Voltage; V _{OL}		Voltage (V _{OD})	10% V _{DD}	
Frequency Stability		±50 ppm over -40°C to 85°C Over all conditions		
Duty Cycle		50% ± 5%		
Rise Time (Tr)/Fall Time (Tf) (10% V _{DD} - 90% V _{DD})		1.5 nS.typ. 3.0 nS. max.		
Current Consumption V _{DD} = +3.3V All values are typical and over operating temperatures.		10 MHz: 17 mA		
		50 MHz: 20 mA		
		100 MHz: 24 mA		
		150 MHz:28 mA		
		200 MHz:33 mA		
		250 MHz: 37 mA		
Current with Output Disabled		16 mA typical		
Start-up Time		10 ms max.		
Aging		±2 ppm max. first year at 25°C; ±10 ppm max. over 10 years		
		Output Enable Function		
OE Pad Input		70% of V _{DD} minimum or no connection to enable output. LVCMOS/LVTTL level.		
XOs: Pad 1		30% of V _{DD} maximum to disable output (high impedance). LVCMOS/LVTTL level.		
VCXOs: Pad 2				
Output Enable Time		200 ns max.		
Output Disable Time		50 ns max.		
	1	Integrated Phase Jitter		
Phase Jitter, rms (12 KHz to 20 MHz)	1.0 pS t	ypical; 1.5 pS max.		
Phase Jitter, rms (1.875 MHz to 20 MHz)	< 100 fs			
		Environmental Performance Specific		
ROHS Status		RoHS compliant, Pb (lead) free in accordance with EU Directive 2002/95/EC 6/6 (2002/95/EC) and WEEE (2002/96/EC)		
Storage Temp. Range		-55°C to 150°C		
Humidity		85% RH, 85°C, 48 hours		
Fine Leak / Gross Leak		MIL-Std-883, method 1014, condition A / MIL-Std-883, method 1014, condition C		
Solderability		MIL-STD-202F method 208E		
Reflow		260°C for 10 sec. 2X.		
Vibration		MIL CTD 2025 mothed 204 250 50 to	MIL-STD-202F method 204, 35G, 50 to 2000 Hz	
vibration		WIL-51D-202F Method 204, 35G, 50 to	2000 112	
Shock		MIL-STD-202F method 204, 35G, 50 to		
Shock		MIL-STD-202F method 213B, test cond		
Shock Resistance to Solvent		MIL-STD-202F method 213B, test cond MIL-STD-202, method 215	di. E, 1000GG ½ sine wave	

Ordering Options:

"x MHz " examples : 125.000000 MHz ; or 12.688375 MHz ; 1250.005600 MHz

Phase Noise Graphs

125 MHz CMOS output

